

disposing a crystallization promoting material in contact with said semiconductor film either before or after said patterning, said crystallization promoting material containing a metal;

crystallizing said patterned semiconductor film provided with said crystallization promoting material by heating; and

etching the peripheral portions of said patterned semiconductor film after said crystallizing.

6. (Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a non-single crystalline semiconductor film to become at least a channel forming region on an insulating surface;

patterning said semiconductor film into a patterned semiconductor film having a peripheral portion;

providing defects and/or stress in said peripheral portion of said patterned semiconductor film simultaneously with said patterning step;

disposing a crystallization promoting material in contact with said semiconductor film, said crystallization promoting material containing a metal;

crystallizing said patterned semiconductor film provided with said crystallization promoting material by heating wherein said metal segregates in said peripheral portion during the crystallization; and

etching said peripheral portion after said crystallizing.

22. (Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a non-single crystalline semiconductor film to become at least a channel forming region on an insulating surface provided over a quartz substrate;

patterning said semiconductor film into a patterned semiconductor film having peripheral portions;

disposing a crystallization promoting material in contact with said semiconductor film either before or after said patterning, said crystallization promoting material containing a metal;

crystallizing said patterned semiconductor film provided with said crystallization promoting material by heating at a temperature of 800 to 1100° C; and

etching the peripheral portions of said patterned semiconductor film after said crystallizing.

23. (Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a non-single crystalline semiconductor film to become at least a channel forming region on an insulating surface provided over a quartz substrate;

patterning said semiconductor film into a patterned semiconductor film having a peripheral portion;

providing defects and/or stress in said peripheral portion of said patterned semiconductor film simultaneously with said patterning step;

disposing a crystallization promoting material in contact with said semiconductor film, said crystallization promoting material containing a metal;

crystallizing said patterned semiconductor film provided with said crystallization promoting material by heating at a temperature of 800 to 1100° C wherein said metal segregates in said peripheral portion during the crystallizing; and

etching said peripheral portion after said crystallizing.

Please add the following new claims 26-28.

26. (New) A method for manufacturing an integrated circuit comprising the steps of:

forming a non-single crystalline semiconductor film to become at least a channel forming region over a quartz substrate;

forming an opening in said semiconductor film by etching a portion of said semiconductor film;

disposing a crystallization promoting material in contact with said semiconductor film either before or after the formation of said opening, said crystallization promoting material containing a metal; and

crystallizing said semiconductor film provided with said crystallization promoting material by heating after the formation of said opening.

27. (New) A method for manufacturing an integrated circuit comprising the steps of:

forming a non-single crystalline semiconductor film to become at least a channel forming region over a quartz substrate;

patterning said semiconductor film into a patterned semiconductor film having peripheral portions;

disposing a crystallization promoting material in contact with said semiconductor film either before or after said

patterning, said crystallization promoting material containing a metal;

crystallizing said patterned semiconductor film provided with said crystallization promoting material by heating at a temperature of 800 to 1100° C; and

etching the peripheral portions of said patterned semiconductor film after said crystallizing.

28. (New) A method for manufacturing an integrated circuit comprising the steps of:

forming a non-single crystalline semiconductor film to become at least a channel forming region over a quartz substrate;

patterning said semiconductor film into a patterned semiconductor film having a peripheral portion;

providing defects and/or stress in said peripheral portion of said patterned semiconductor film simultaneously with said patterning step;

disposing a crystallization promoting material in contact with said semiconductor film, said crystallization promoting material containing a metal;

crystallizing said patterned semiconductor film provided with said crystallization promoting material by heating